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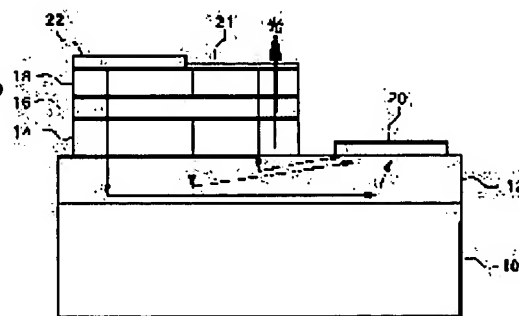
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(54) GALLIUM NITRIDE COMPOUND SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To improve a light fetching efficiency in a gallium nitride light emitting element.

SOLUTION: The gallium nitride light emitting element comprises an n-type GaN buffer layer 12, an n-type GaN layer 14, an InGaN light emitting layer 16, a p-type GaN layer 18, an n-type electrode 20, and a p-type electrode 22 sequentially formed on a sapphire substrate 10. A ZnO transparent electrode 21 is formed adjacent to the electrode 22 on the p-type GaN layer. A current is uniformly supplied to the light emitting layer via the electrode 21, and a light from the light emitting layer is transmitted and fetched externally.



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